

Low Phase Noise XO with multipliers (for HF Fund. and 3rd O.T.)

FEATURES

- 100MHz to 200MHz Fundamental or 3rd Overtone Crystal input.
- Output range: 100 – 200MHz (no multiplication), 200 – 400MHz (2x multiplier) or 400 – 700MHz (4x multiplier).
- Available outputs: PECL, LVDS, or CMOS (High Drive (30mA) or Standard Drive (10mA) output).
- Supports 3.3V-Power Supply.
- Available in die form.
- Thickness 10 mil.

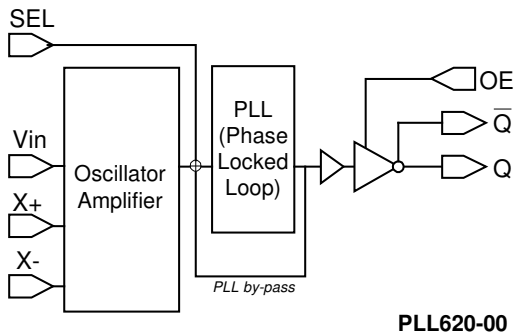
DESCRIPTION

The PLL620-00 is an XO IC specifically designed to work with high frequency fundamental and third overtone crystals. Its design was optimized to tolerate higher limits of interelectrode capacitance and bonding capacitance to improve yield. It achieves very low current into the crystal resulting in better overall stability. It is ideal for XO applications requiring LVDS or PECL output levels at high frequencies.

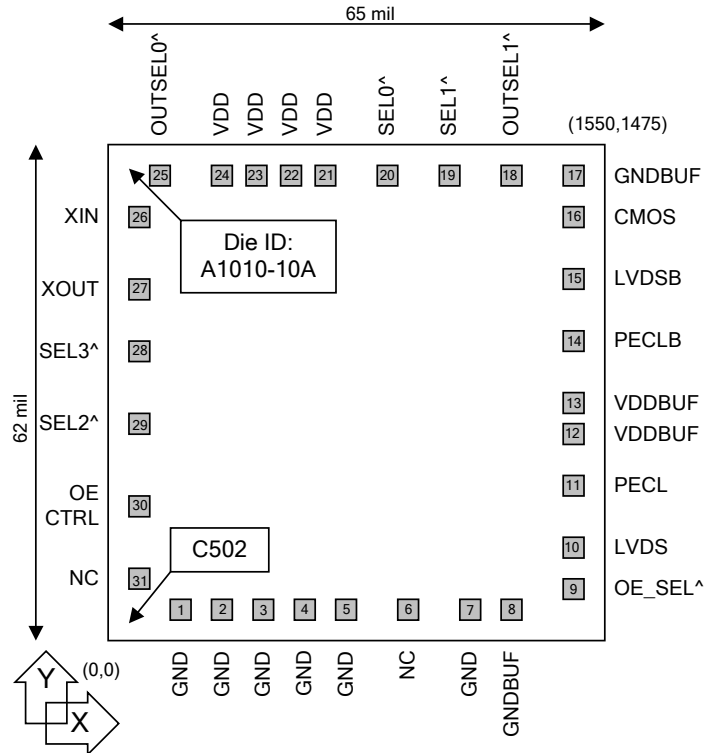
DIE SPECIFICATIONS

| Name | Value |
|----------------|-----------------------|
| Size | 62 x 65 mil |
| Reverse side | GND |
| Pad dimensions | 80 micron x 80 micron |
| Thickness | 10 mil |

BLOCK DIAGRAM



DIE CONFIGURATION



OUTPUT SELECTION AND ENABLE

| OUTSEL1 (Pad #18) | OUTSEL0 (Pad #25) | Selected Output |
|-------------------|-------------------|-----------------|
| 0 | 0 | High Drive CMOS |
| 0 | 1 | Standard CMOS |
| 1 | 0 | LVDS |
| 1 | 1 | PECL (default) |

| OE_SELECT (Pad #9) | OE_CTRL (Pad #30) | State |
|--------------------|-------------------|----------------|
| 0 | 0 | Tri-state |
| | 1 (Default) | Output enabled |
| 1 (Default) | 0 (Default) | Output enabled |
| | 1 | Tri-state |

Pad #9: Bond to GND to set to "0", bond to VDD to set to "1"
 Pad #30: Logical states defined by PECL levels if OE_SELECT (pad #9) is "1"
 Logical states defined by CMOS levels if OE_SELECT is "0"

Low Phase Noise XO with multipliers (for HF Fund. and 3rd O.T.) FREQUENCY SELECTION TABLE

| SEL3 (Pad #28) | SEL2 (Pad #29) | SEL1 (Pad #19) | SEL0 (Pad #20) | Selected Multiplier |
|-------------------|-------------------|-------------------|-------------------|----------------------------|
| 1 | 0 | 1 | 1 | Fin x 4 |
| 1 | 1 | 1 | 0 | Fin x 2 |
| 1 | 1 | 1 | 1 | No multiplication (no PLL) |

All pads have internal pull-ups (default value is 1). Bond to GND to set to 0.

ELECTRICAL SPECIFICATIONS

1. Absolute Maximum Ratings

| PARAMETERS | SYMBOL | MIN. | MAX. | UNITS |
|-----------------------------------|----------|------|--------------|-------|
| Supply Voltage | V_{DD} | | 4.6 | V |
| Input Voltage, dc | V_I | -0.5 | $V_{DD}+0.5$ | V |
| Output Voltage, dc | V_O | -0.5 | $V_{DD}+0.5$ | V |
| Storage Temperature | T_S | -65 | 150 | °C |
| Ambient Operating Temperature* | T_A | -40 | 85 | °C |
| Junction Temperature | T_J | | 125 | °C |
| Lead Temperature (soldering, 10s) | | | 260 | °C |
| ESD Protection, Human Body Model | | | 2 | kV |

Exposure of the device under conditions beyond the limits specified by Maximum Ratings for extended periods may cause permanent damage to the device and affect product reliability. These conditions represent a stress rating only, and functional operations of the device at these or any other conditions above the operational limits noted in this specification is not implied.

* Note: Operating Temperature is guaranteed by design for all parts (COMMERCIAL and INDUSTRIAL), but tested for COMMERCIAL grade only.

2. Crystal Specifications

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|-----------------------------|--------------|--|------|------|------|----------|
| Crystal Resonator Frequency | F_{XIN} | Fundamental or 3 rd overtone* | 100 | | 200 | MHz |
| Crystal Loading Rating | C_L (xtal) | Die only | | 3.0 | | pF |
| Interelectrode Capacitance | C_0 | | | | 3 | pF |
| Recommended ESR | R_E | $F_{XIN}<160\text{MHz}$ and $C_0<3.0\text{pF}$ | | | 30 | Ω |
| | | $F_{XIN}<200\text{MHz}$ and $C_0<3.0\text{pF}$ | | | 25 | Ω |
| | | $F_{XIN}<200\text{MHz}$ and $C_0<2.5\text{pF}$ | | | 30 | Ω |

* Note: 3rd overtone crystals require an external resistor between XIN and XOUT to prevent the fundamental from oscillating.

3. General Electrical Specifications

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|---------------------------------|----------|---------------------------------|------|----------|-----------|-------|
| Supply Current (Loaded Outputs) | I_{DD} | PECL/LVDS/CMOS | | | 100/80/40 | mA |
| Operating Voltage | V_{DD} | | 2.97 | | 3.63 | V |
| Output Clock Duty Cycle | | @ 50% V_{DD} (CMOS) | 45 | 50 | 55 | % |
| | | @ 1.25V (LVDS) | 45 | 50 | 55 | % |
| | | @ $V_{DD} - 1.3\text{V}$ (PECL) | 45 | 50 | 55 | % |
| Short Circuit Current | | | | ± 50 | | mA |

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4. Jitter Specifications

| PARAMETERS | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|---------------------------------|--|------|------|------|-------|
| Period jitter RMS | At 155.52MHz, with capacitive decoupling between VDD and GND. Over 10,000 cycles | | 2.5 | | ps |
| Period jitter peak-to-peak | | | 18.5 | 20 | |
| Accumulated jitter RMS | At 155.52MHz, with capacitive decoupling between VDD and GND. Over 1,000,000 cycles. | | 2.5 | | ps |
| Accumulated jitter peak-to-peak | | | 24 | 27 | |
| Random Jitter | "RJ" measured on Wavecrest SIA 3000 | | 2.5 | | ps |
| Integrated jitter RMS at 155MHz | Integrated 12 kHz to 20 MHz | | 0.3 | 0.4 | ps |
| Period jitter RMS | At 622.08MHz, with capacitive decoupling between VDD and GND. Over 10,000 cycles | | 11 | | ps |
| Period jitter peak-to-peak | | | 45 | 49 | |
| Accumulated jitter RMS | At 622.08MHz, with capacitive decoupling between VDD and GND. Over 1,000,000 cycles. | | 11 | | ps |
| Accumulated jitter peak-to-peak | | | 24 | 27 | |
| Random Jitter | "RJ" measured on Wavecrest SIA 3000 | | 3 | | ps |
| Integrated jitter RMS at 622MHz | Integrated 12 kHz to 20 MHz | | 1.6 | 1.8 | ps |

Note: Higher Q factor of 3rd overtone crystals will result in even better jitter performance.
Measured on Wavecrest SIA 3000

5. Phase Noise Specifications

| PARAMETERS | FREQUENCY | @10Hz | @100Hz | @1kHz | @10kHz | @100kHz | UNITS |
|---------------------------------|-----------|-------|--------|-------|--------|---------|--------|
| Phase Noise relative to carrier | 155.52MHz | -75 | -95 | -125 | -140 | -145 | dBc/Hz |
| | 622.08MHz | -75 | -95 | -110 | -125 | -120 | |

Note: Higher Q factor of 3rd overtone crystals will result in even better phase noise performance.

6. CMOS Electrical Specifications

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|--|-----------------|--|------|------|------|-------|
| Output drive current (High Drive) | I _{OH} | V _{OH} = V _{DD} -0.4V, V _{DD} =3.3V | 30 | | | mA |
| | I _{OL} | V _{OL} = 0.4V, V _{DD} = 3.3V | 30 | | | mA |
| Output drive current (Standard Drive) | I _{OH} | V _{OH} = V _{DD} -0.4V, V _{DD} =3.3V | 10 | | | mA |
| | I _{OL} | V _{OL} = 0.4V, V _{DD} = 3.3V | 10 | | | mA |
| Output Clock Rise/Fall Time (Standard Drive) | | 0.3V ~ 3.0V with 15 pF load | | 2.4 | | ns |
| Output Clock Rise/Fall Time (High Drive) | | 0.3V ~ 3.0V with 15 pF load | | 1.2 | | |

Low Phase Noise XO with multipliers (for HF Fund. and 3rd O.T.)

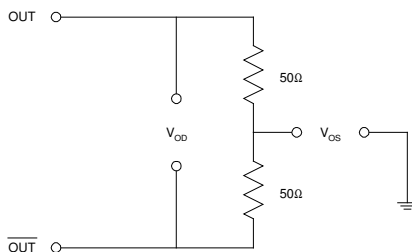
7. LVDS Electrical Characteristics

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|------------------------------|-----------------|--|-------|---------|----------|---------|
| Output Differential Voltage | V_{OD} | $R_L = 100 \Omega$ (see figure) | 247 | 355 | 454 | mV |
| V_{DD} Magnitude Change | ΔV_{OD} | | -50 | | 50 | mV |
| Output High Voltage | V_{OH} | | 1.4 | 1.6 | V | |
| Output Low Voltage | V_{OL} | | 0.9 | 1.1 | V | |
| Offset Voltage | V_{OS} | | 1.125 | 1.2 | 1.375 | V |
| Offset Magnitude Change | ΔV_{OS} | | 0 | 3 | 25 | mV |
| Power-off Leakage | I_{OXD} | $V_{out} = V_{DD}$ or GND $V_{DD} = 0V$ | | ± 1 | ± 10 | μA |
| Output Short Circuit Current | I_{OSD} | | | -5.7 | -8 | mA |

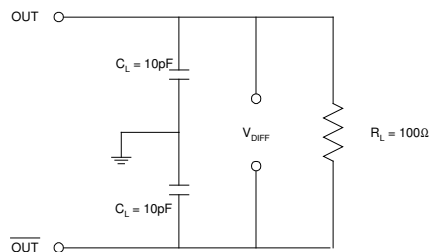
8. LVDS Switching Characteristics

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|------------------------------|--------|---|------|------|------|-------|
| Differential Clock Rise Time | t_r | $R_L = 100 \Omega$ $C_L = 10 \text{ pF}$ (see figure) | 0.2 | 0.7 | 1.0 | ns |
| Differential Clock Fall Time | t_f | | 0.2 | 0.7 | 1.0 | ns |

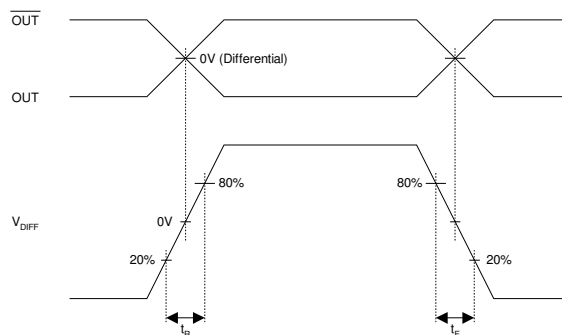
LVDS Levels Test Circuit



LVDS Switching Test Circuit



LVDS Transistion Time Waveform



Low Phase Noise XO with multipliers (for HF Fund. and 3rd O.T.)

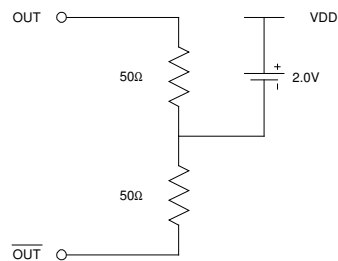
9. PECL Electrical Characteristics

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | MAX. | UNITS |
|---------------------|----------|--|------------------|------------------|-------|
| Output High Voltage | V_{OH} | $R_L = 50 \Omega$ to $(V_{DD} - 2V)$ (see figure) | $V_{DD} - 1.025$ | | V |
| Output Low Voltage | V_{OL} | | | $V_{DD} - 1.620$ | V |

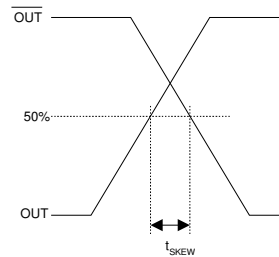
10. PECL Switching Characteristics

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|-----------------|--------|----------------|------|------|------|-------|
| Clock Rise Time | t_r | @20/80% - PECL | | 0.6 | 1.5 | ns |
| Clock Fall Time | t_f | @80/20% - PECL | | 0.5 | 1.5 | ns |

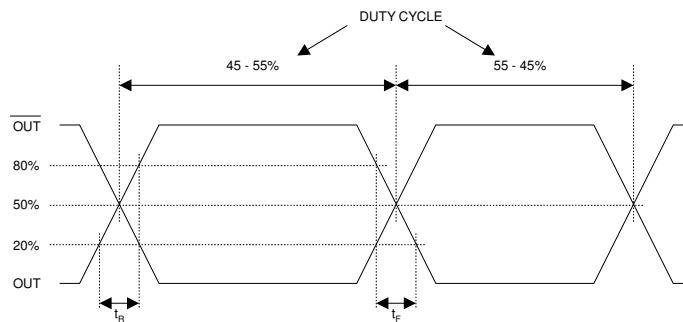
PECL Levels Test Circuit



PECL Output Skew



PECL Transition Time Waveform



Low Phase Noise XO with multipliers (for HF Fund. and 3rd O.T.)
PAD ASSIGNMENT

| Pad # | Name | X (μm) | Y (μm) | Description |
|-------|-----------|--------|--------|---|
| 1 | GND | 248 | 109 | Ground. |
| 2 | GND | 361 | 109 | Ground. |
| 3 | GND | 473 | 109 | Ground. |
| 4 | GND | 587 | 109 | Ground. |
| 5 | GND | 702 | 109 | Ground. |
| 6 | N/C | 874 | 109 | No Connection. |
| 7 | GND | 1042 | 109 | Ground. |
| 8 | GNDBUF | 1171 | 109 | Ground, Buffer circuitry. |
| 9 | OE_SELECT | 1400 | 125 | Used to select between PECL or CMOS logic states for OE. See Output Selection and Enable table on page 1. Internal pull up. |
| 10 | LVDS | 1400 | 259 | LVDS output. |
| 11 | PECL | 1400 | 476 | PECL output. |
| 12 | VDDBUF | 1400 | 616 | 3.3V power supply, Buffer circuitry. |
| 13 | VDDBUF | 1400 | 716 | 3.3V power supply, Buffer circuitry. |
| 14 | PECLB | 1400 | 871 | Complementary PECL output. |
| 15 | LVDSB | 1400 | 1089 | Complementary LVDS output. |
| 16 | CMOS | 1400 | 1227 | CMOS output |
| 17 | GNDBUF | 1389 | 1365 | Ground, Buffer Circuitry. |
| 18 | OUTSEL1 | 1232 | 1365 | Used to select CMOS, PECL or LVDS output type. See Output Selection and Enable table on page 1. Internal pull up. |
| 19 | SEL1 | 1042 | 1365 | Used to select multiplication factor. See Frequency Selection table on page 1. Internal pull up. |
| 20 | SEL0 | 854 | 1365 | Used to select multiplication factor. See Frequency Selection table on page 1. Internal pull up. |
| 21 | VDD | 659 | 1365 | 3.3V power supply. |
| 22 | VDD | 559 | 1365 | 3.3V power supply. |
| 23 | VDD | 459 | 1365 | 3.3V power supply. |
| 24 | VDD | 358 | 1365 | 3.3V power supply. |
| 25 | OUTSEL0 | 194 | 1365 | Used to select CMOS, PECL or LVDS output type. See Output Selection and Enable table on page 1. Internal pull up. |
| 26 | XIN | 109 | 1223 | Crystal input. See crystal specification page 2. |
| 27 | XOUT | 109 | 1017 | Crystal output. See crystal specification page 2. |
| 28 | SEL3 | 109 | 858 | Used to select multiplication factor. See Frequency Selection table on page 1. Internal pull up. |
| 29 | SEL2 | 109 | 646 | Used to select multiplication factor. See Frequency Selection table on page 1. Internal pull up. |
| 30 | OE_CTRL | 109 | 397 | Used to enable/disable the output(s). See Output Selection and Enable table on page 1. |
| 31 | NC | 109 | 181 | No Connection. |

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ORDERING INFORMATION

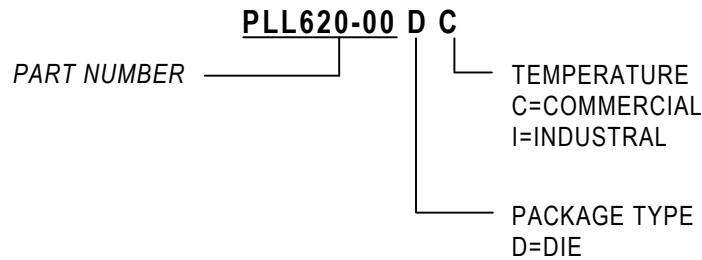
For part ordering, please contact our Sales Department:

47745 Fremont Blvd., Fremont, CA 94538, USA

Tel: (510) 492-0990 Fax: (510) 492-0991

PART NUMBER

The order number for this device is a combination of the following:
Device number, Package type and Operating temperature range



| <u>Order Number</u> | <u>Marking</u> | <u>Package Option</u> |
|---------------------|----------------|-----------------------|
| PLL620-00DC | P620-00DC | Die – Waffle Pack |

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